

Abstracts

12W Monolithic X-Band HBT Power Amplifier

M.A. Khatibzadeh, B. Bayraktaroglu and T. Kim. "12W Monolithic X-Band HBT Power Amplifier." 1992 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 92.1 (1992 [MCS]): 47-50.

Monolithic, 2-stage X-band power amplifiers have been designed and fabricated using AlGaAs/GaAs HBTs. Output power levels of up to 12.5 W cw have been demonstrated at 9.2 GHz from single-chip HBT amplifiers measuring 3.8 mm x 4.7 mm in size. To our knowledge, this is the highest cw output power level reported at X-band frequencies for any monolithic power amplifier and highlights the advantages of HBT technology for microwave solid-state power applications.

[Return to main document.](#)